



Automotive N-Channel 75 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V _{DS} (V)	75
R _{DS(on)} (Ω) at V _{GS} = 10 V	0.0048
I _D (A)	120
Configuration	Single

FEATURES

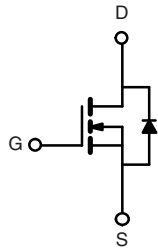
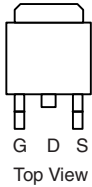
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualified^d
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

AUTOMOTIVE GRADE



RoHS COMPLIANT HALOGEN FREE

TO-263



N-Channel MOSFET

ORDERING INFORMATION	
Package	TO-263
Lead (Pb)-free and Halogen-free	SQM120N08-05-GE3

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	75	V
Gate-Source Voltage		V _{GS}	± 20	
Continuous Drain Current	T _C = 25 °C ^a	I _D	120	A
	T _C = 125 °C		106	
Continuous Source Current (Diode Conduction) ^a		I _S	120	
Pulsed Drain Current ^b		I _{DM}	480	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	66	
Single Pulse Avalanche Energy		E _{AS}	217	
Maximum Power Dissipation ^b	T _C = 25 °C	P _D	375	W
	T _C = 125 °C		125	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	40	°C/W
Junction-to-Case (Drain)		R _{thJC}	0.4	

Notes

- Package limited.
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR-4 material).
- Parametric verification ongoing.



SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		75	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2.5	-	4.0	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 75 V	-	-	1.0	μA
		V _{GS} = 0 V	V _{DS} = 75 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 75 V, T _J = 175 °C	-	-	250	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	120	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 30 A	-	0.0039	0.0048	Ω
		V _{GS} = 10 V	I _D = 30 A, T _J = 125 °C	-	-	0.0087	
		V _{GS} = 10 V	I _D = 30 A, T _J = 175 °C	-	-	0.0110	
Forward Transconductance ^{a, b}	g _{fs}	V _{DS} = 15 V, I _D = 30 A		-	102	-	S
Dynamic^b							
Input Capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	8158	10 200	pF
Output Capacitance	C _{oss}			-	865	1085	
Reverse Transfer Capacitance	C _{rss}			-	567	710	
Total Gate Charge ^c	Q _g	V _{GS} = 10 V	V _{DS} = 35 V, I _D = 110 A	-	141	212	nC
Gate-Source Charge ^c	Q _{gs}			-	32.6	-	
Gate-Drain Charge ^c	Q _{gd}			-	39.1	-	
Gate Resistance	R _g	f = 1 MHz		0.6	1.2	1.9	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 35 V, R _L = 0.32 Ω I _D ≅ 110 A, V _{GEN} = 10 V, R _g = 1 Ω		-	19	29	ns
Rise Time ^c	t _r			-	31	47	
Turn-Off Delay Time ^c	t _{d(off)}			-	55	83	
Fall Time ^c	t _f			-	15	23	
Source-Drain Diode Ratings and Characteristics^b							
Pulsed Current ^a	I _{SM}			-	-	480	A
Forward Voltage	V _{SD}	I _F = 100 A, V _{GS} = 0 V		-	0.9	1.5	V

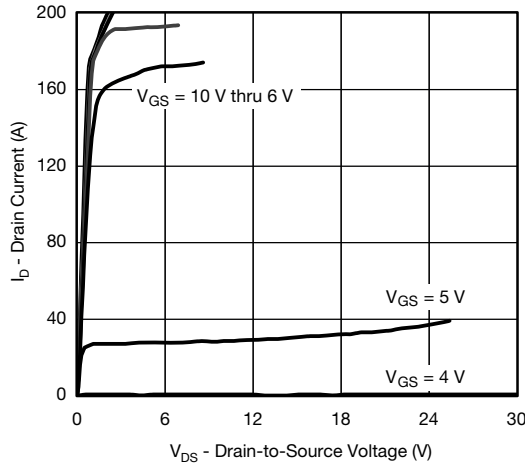
Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

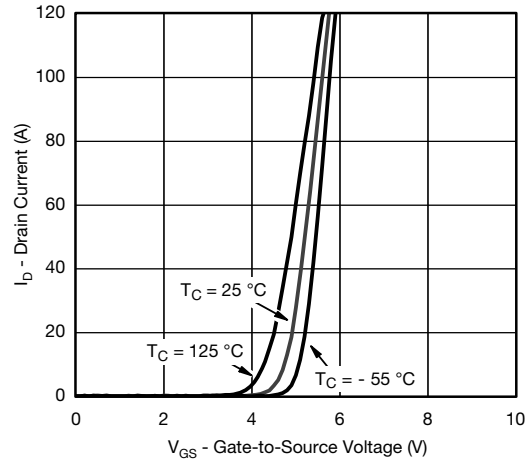
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



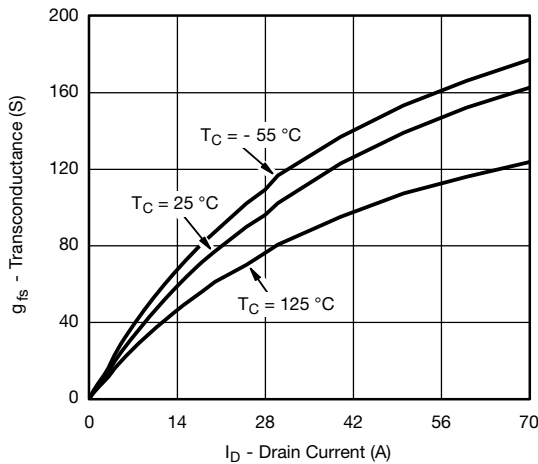
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



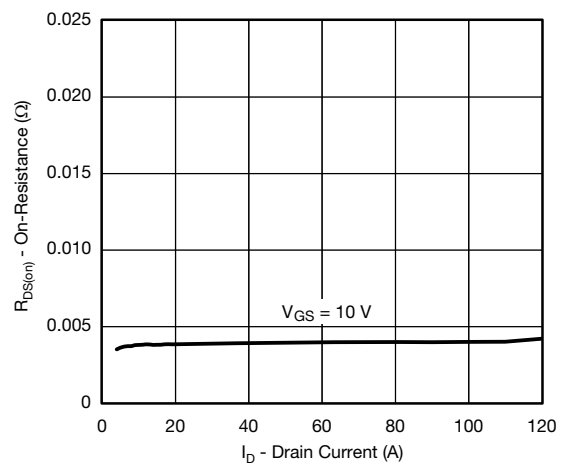
Output Characteristics



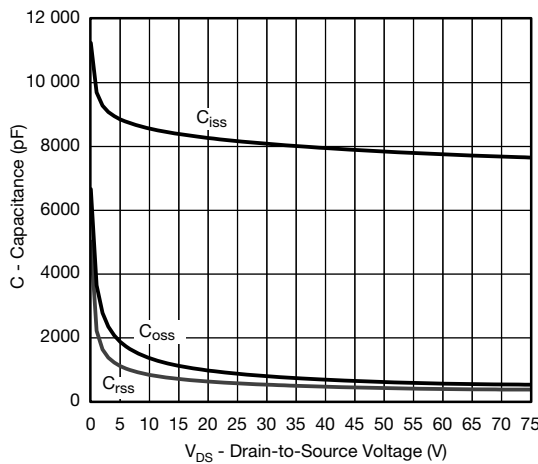
Transfer Characteristics



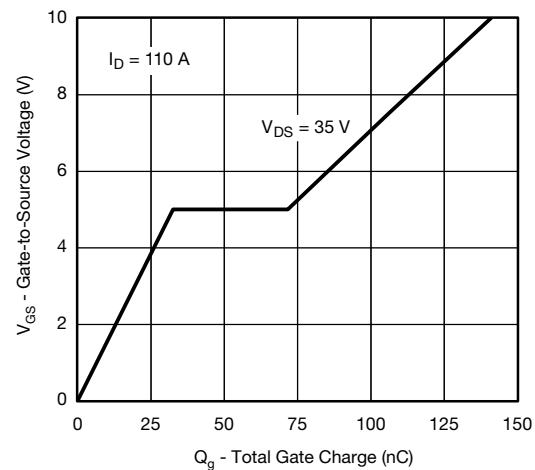
Transconductance



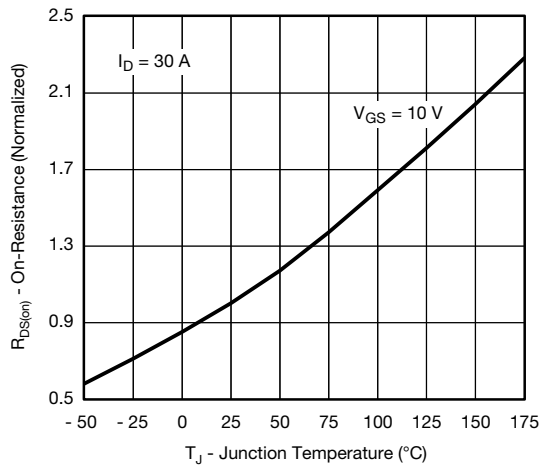
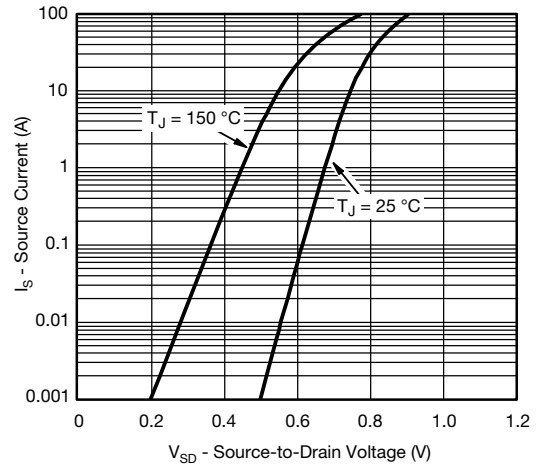
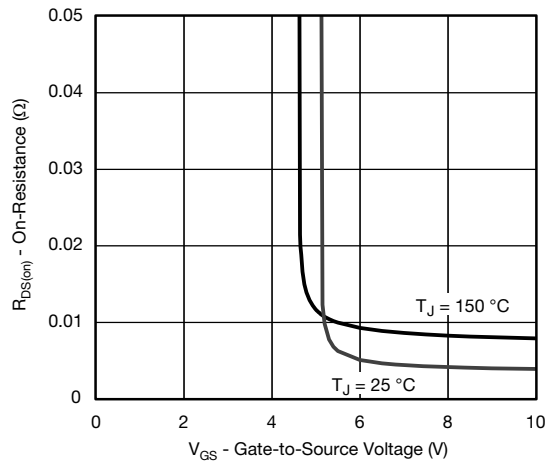
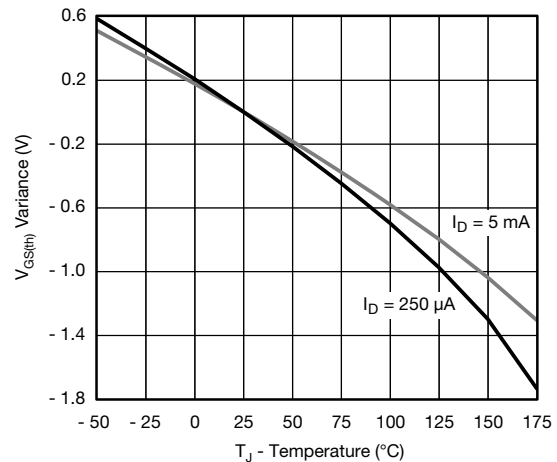
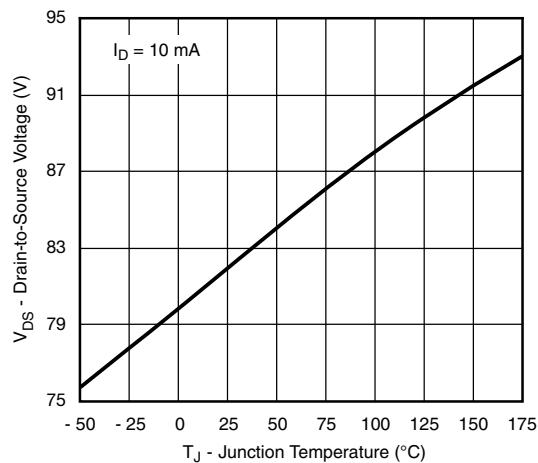
On-Resistance vs. Drain Current



Capacitance

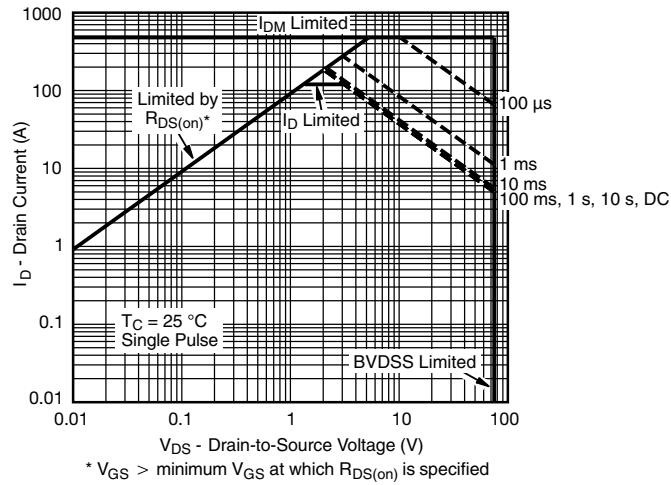


Gate Charge

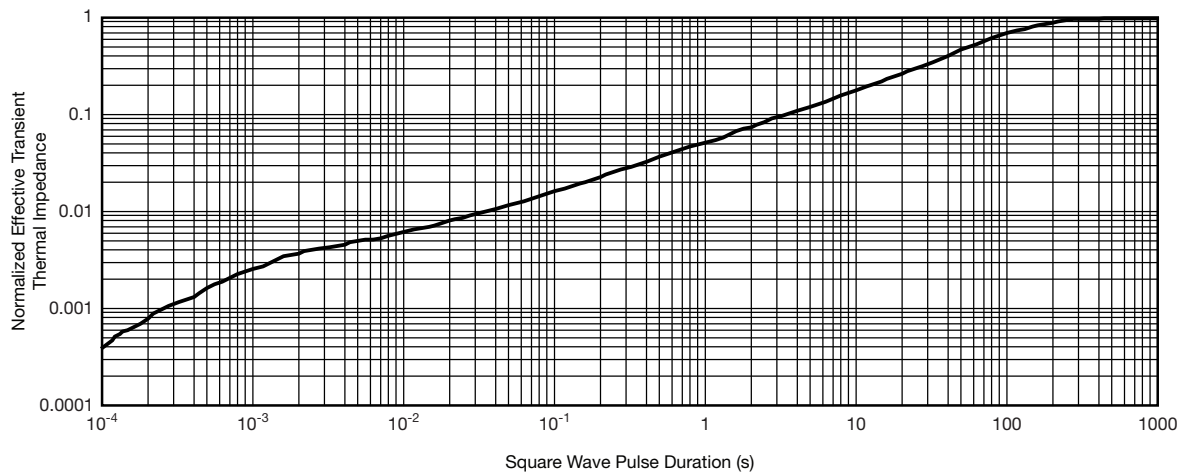
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)

On-Resistance vs. Junction Temperature

Source Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



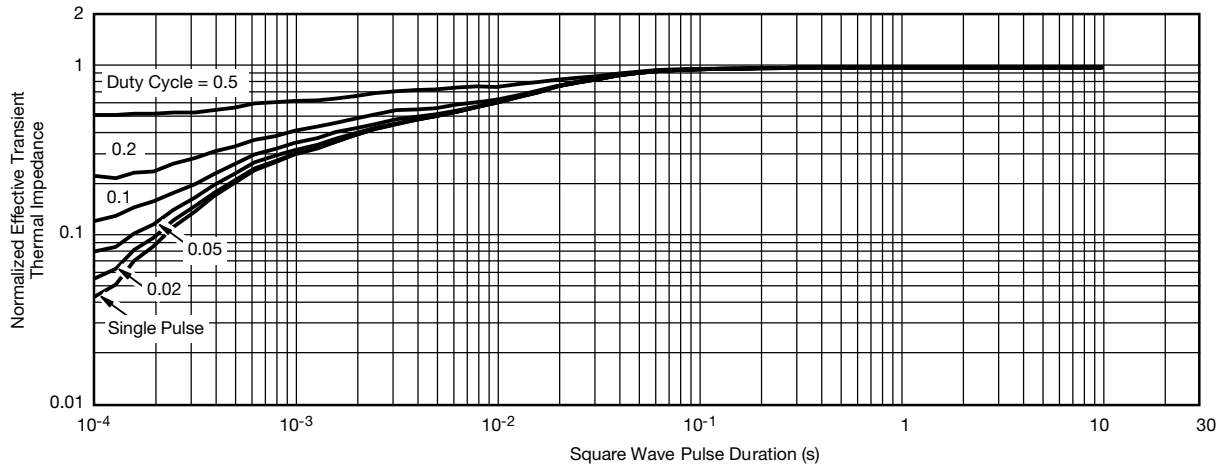
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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